Applied Surface Science 39 (1989) 597–602
North-Holland, Amsterdam

AUTHOR INDEX

Abstreiter, G., see Brunner 39 (1989) 116
Aizenberg, I.A., I.R. Moskvina and S.N. Nosenko, The changes in Si surface roughness and their diagnostics 39 (1989) 473
Andersson, M.O. and O. Engström, Atomic relaxation of Si–SiO_2 interface states measured by a photo-depopulation technique 39 (1989) 289
Anton, J., see Gual 39 (1989) 144

Balk, P., see Saettler 39 (1989) 259
Balk, P., see Baten 39 (1989) 266
Balland, B., J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210
Baten, J., M. Offenberg, U. Emmerichs, P. Balk, P.J. Grunthaner and S. Ewert, Diffusion of cobalt and titanium in SiO_2 39 (1989) 266
Batey, J., E. Tierney, J. Stasiak and T.N. Nguyen, Plasma-enhanced CVD of high quality insulating films 39 (1989) 1
Bath, A., P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135
Bauch, W., K. Jäger and R. Hezel, Effect of Cs contamination on the interface state density of MNOS capacitors 39 (1989) 356
Baunach, R., see Spitzer 39 (1989) 192
Baunach, R. and A. Spitzer, Simulation of charge transport and trapping in MIS structures with triple-layer dielectrics 39 (1989) 200
Beahan, P., see Hall 39 (1989) 57
Bellens, R., see Maes 39 (1989) 523
Belyi, V.I., T.P. Smirnova and N.F. Zakharchuk, Phase composition and structure of native oxides on $A^{III}B^{V}$ semiconductors 39 (1989) 161
Benamar, A., see Balland 39 (1989) 210
Bjorkman, C.H., see Fitch 39 (1989) 103
Blanconnier, P., see Le Bellego 39 (1989) 168
Bogdanov, S.V., P.P. Povarov, V.E. Shubin and D.A. Shushakov, Investigation of MIS structures using avalanche multiplication 39 (1989) 381
Boher, P., see Gual 39 (1989) 144
Brox, M., F. Hofmann and W. Weber, Spatial distribution of damage caused by 6.4 eV photon irradiation in the gate oxide of MOSFET's 39 (1989) 429
Brunner, K., G. Abstreiter, B.O. Kolbesen and H.W. Meul, Strain at Si–SiO_2 interfaces studied by micro-Raman spectroscopy 39 (1989) 116
Buchanan, D.A., M.V. Fischetti and D.J. DiMaria, Coulombic and neutral electron trapping centers in SiO_2 39 (1989) 420
Bureau, J.C., see Balland 39 (1989) 210

Celler, G.K. and L.E. Trimble, Formation of SiO at Si/SiO_2 interface and its influence on transport of Group V dopants and Ge in SiO_2 39 (1989) 245

Cheng, Y.C., see Wong 39 (1989) 493
Cros, Y., see Michailos 39 (1989) 16

De Keersmaecker, R.F., see Heyns 39 (1989) 327
De Keersmaecker, R.F., see Oude Elferink 39 (1989) 219
De Keersmaecker, R.F., see Dooms 39 (1989) 227
Deal, B.E., see DeLarios 39 (1989) 89
DeLarios, J.M., C.R. Helms, D.B. Kao and B.E. Deal, Parallel oxidation model for Si including both molecular and atomic oxygen mechanisms 39 (1989) 89
Delima, J.J., see Snell 39 (1989) 368
Denisse, C.M.M., H.E. Smulders, F.H.P.M. Habraken and W.F. van der Weg, Oxidation of plasma enhanced chemical vapour deposited silicon nitride and oxynitride films 39 (1989) 25
DiMaria, D.J., see Buchanan 39 (1989) 420
DiMaria, D.J., see Fischetti 39 (1989) 578
Dooms, E.E., see Oude Elferink 39 (1989) 219
Dooms, E.E., M.M. Heyns and R.F. De Keersmaecker, Characterization of 30 nm nitrided oxides fabricated by rapid thermal nitridation 39 (1989) 227
Dubray, J.J., see Balland 39 (1989) 210

Eccleston, W., see Hall 39 (1989) 57
Eccleston, W., see Zhang 39 (1989) 374
Edwards, A.H., A critical assessment of the overcoordination model for the P_b center at the $\langle 111 \rangle$ Si/SiO_2 interface 39 (1989) 309
Emmerichs, U., see Baten 39 (1989) 266
Engström, O., see Andersson 39 (1989) 289
Evtukh, A.A., see Litovchenko 39 (1989) 238
Ewert, S., see Baten 39 (1989) 266

Ferretti, R., see Prasad 39 (1989) 348
Fischetti, M.V., see Buchanan 39 (1989) 420
Fischetti, M.V., S.E. Laux and D.J. DiMaria, The physics of hot-electron degradation of Si MOSFET's: can we understand it? 39 (1989) 578
Fitch, J.T., C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
Fountain, G.G., see Lucovsky 39 (1989) 33

Gibbings, C.J., see Hall 39 (1989) 57
Gill, A., see Young 39 (1989) 364
Glachant, A., see Balland 39 (1989) 210
Groeseneken, G., see Maes 39 (1989) 523
Grundner, M., see Hahn 39 (1989) 436
Grunthaner, P.J., see Baten 39 (1989) 266
Gual, J., J. Samitier, J.R. Morante, J. Anton, P. Boher and M. Renaud, Isolation quality in passivated semi-insulating GaAs analyzed by leakage current transients 39 (1989) 144

Habraken, F.H.P.M., see Denisse 39 (1989) 25
Habraken, F.H.P.M., see Oude Elferink 39 (1989) 219
Hahn, P.O., M. Grundner, A. Schnegg and H. Jacob, Correlation of surface morphology and chemical state of Si surfaces to electrical properties 39 (1989) 436

Hahn, P.O., see Pietsch 39 (1989) 457
Hall, S., J.F. Zhang, S. Taylor, W. Eccleston, P. Beahan, G.T. Tatlock, C.J. Gibbings, C. Smith and C. Tuppen, Assessment of plasma-grown oxides on Si:Ge substrates 39 (1989) 57
Hartnagel, H.L., see Longère 39 (1989) 151
Helms, C.R., see DeLarios 39 (1989) 89
Henzler, M., see Pietsch 39 (1989) 457
Heremans, P., see Maes 39 (1989) 523
Heyers, K., see Saettler 39 (1989) 259
Heyns, M.M., see Oude Elferink 39 (1989) 219
Heyns, M.M., see Dooms 39 (1989) 227
Heyns, M.M., D. Krishna Rao and R.F. De Keersmaecker, Oxide field dependence of Si–SiO_2 interface state generation and charge trapping during electron injection 39 (1989) 327
Hezel, R., see Bauch 39 (1989) 356
Hofmann, F., see Brox 39 (1989) 429
Hönlein, W. and H. Reisinger, ONO technology 39 (1989) 178

Jackson, W.B., Defect kinetics in hydrogenated amorphous silicon MIS structures 39 (1989) 273
Jacob, H., see Hahn 39 (1989) 436
Jäger, K., see Bauch 39 (1989) 356
Jäntsch, O., Statistics of random telegraph signals in MOSFET's 39 (1989) 486
Johnson, N.M., Wei Shan and P.Y. Yu, A test of the dangling-orbital versus overcoordination models for the P_b center at the Si–SiO_2 interface 39 (1989) 301
Jousse, D., J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412

Kanicki, J., see Lenahan 39 (1989) 392
Kanicki, J., see Jousse 39 (1989) 412
Kao, D.B., see DeLarios 39 (1989) 89
Karmann, A. and M. Schulz, Characterization of individual defects in MOSFET's 39 (1989) 500
Kim, S.S., see Lucovsky 39 (1989) 33
Kirton, M.J., see Uren 39 (1989) 479
Koch, F., see Müller 39 (1989) 127
Koch, F., see Ye 39 (1989) 339
Kolbesen, B.O., see Brunner 39 (1989) 116
Korshunov, A.N., see Salman 39 (1989) 141
Krawczyk, S.K., see Longère 39 (1989) 151
Krick, D.T., see Lenahan 39 (1989) 392
Krishna, K.V., see Snell 39 (1989) 368
Krishna Rao, D., see Heyns 39 (1989) 327

Lauer, V., see Saettler 39 (1989) 259
Laux, S.E., see Fischetti 39 (1989) 578
Le Bellego, Y., J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168
Lenahan, P.M., D.T. Krick and J. Kanicki, The nature of the dominant deep trap in amorphous silicon nitride films: evidence for a negative correlation energy 39 (1989) 392

Lenahan, P.M., see Warren 39 (1989) 406
Lepley, B., see Bath 39 (1989) 135
Litovchenko, V.G., V.G. Popov and A.A. Evtukh, Characteristics of the insulator–semiconductor (IS) systems with a graded-bandgap insulator at high electric fields 39 (1989) 238
Longère, J.Y., K. Schohe, S.K. Krawczyk, R. Schütz and H.L. Hartnagel, Passivation of InP surfaces controlled by photoluminescence measurements 39 (1989) 151
Lucovsky, G., D.V. Tsu, S.S. Kim, R.J. Markunas and G.G. Fountain, Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD) 39 (1989) 33
Lucovsky, G., see Fitch 39 (1989) 103
Lyon, S.A., Interface states generated by the injection of electrons and holes into SiO_2 39 (1989) 552
Lysenko, V.S., A.N. Nazarov, I.N. Osiyuk and V.I. Turchanikov, Transformation of Si–SiO_2–Al structures under RF-plasma treatment (Extended Abstract) 39 (1989) 388

Maes, H.E., G. Groeseneken, P. Heremans and R. Bellens, Understanding of the hot carrier degradation behaviour of MOSFET's by means of the charge pumping technique 39 (1989) 523
Markunas, R.J., see Lucovsky 39 (1989) 33
Meul, H.W., see Brunner 39 (1989) 116
Michailos, J. and Y. Cros, Influence of helium dilution on physico-chemical and defect properties of PECVD silicon oxynitride films 39 (1989) 16
Morante, J.R., see Gual 39 (1989) 144
Moskvina, I.R., see Aizenberg 39 (1989) 473
Müller, F., N. Schwarz, V. Petrova-Koch and F. Koch, Vibration spectroscopy for surface layers on Si 39 (1989) 127

Nazarov, A.N., see Lysenko 39 (1989) 388
Nguyen, T.N., see Batey 39 (1989) 1
Nissan-Cohen, Y., The effect of hydrogen on hot carrier and radiation immunity of MOS devices 39 (1989) 511
Nosenko, S.N., see Aizenberg 39 (1989) 473

Offenberg, M., see Saettler 39 (1989) 259
Offenberg, M., see Baten 39 (1989) 266
Osiyuk, I.N., see Lysenko 39 (1989) 388
Oude Elferink, J.B., F.H.P.M. Habraken, W.F. van der Weg, E. Dooms, M. Heyns and R. De Keersmaecker, Rapid thermal nitridation of SiO_2 films 39 (1989) 219
Owen, A.E., see Snell 39 (1989) 368

Petrova-Koch, V., see Müller 39 (1989) 127
Pietsch, G.J., M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457

Pollak, F.H., see Fitch 39 (1989) 103
Popov, V.G., see Litovchenko 39 (1989) 238
Povarov, P.P., see Bogdanov 39 (1989) 381
Prasad, S. and R. Ferretti, Influence of annealing on interfaces of MOS structures with RTO oxides 39 (1989) 348
Praseuth, J.P., see Le Bellego 39 (1989) 168

Reisinger, H., see Hönlein 39 (1989) 178
Renaud, J.C., see Le Bellego 39 (1989) 168
Renaud, M., see Gual 39 (1989) 144
Rigo, S., see Trimaille 39 (1989) 65
Robinson, B., see Warren 39 (1989) 406

Saettler, M., V. Lauer, M. Offenberg, K. Heyers and P. Balk, Effects of ion implantation on the interfacial properties of MOS systems 39 (1989) 259
Salman, E.G., A.N. Korshunov and V.N. Vertoprakhov, A DLTS study of InAs MIS structures (Extended Abstract) 39 (1989) 141
Samitier, J., see Gual 39 (1989) 144
Schnegg, A., see Hahn 39 (1989) 436
Schohe, K., see Longère 39 (1989) 151
Schoonman, J., see Bath 39 (1989) 135
Schulz, M., see Karmann 39 (1989) 500
Schütz, R., see Longère 39 (1989) 151
Schwarz, N., see Müller 39 (1989) 127
Shubin, V.E., see Bogdanov 39 (1989) 381
Shushakov, D.A., see Bogdanov 39 (1989) 381
Smirnova, T.P., see Belyi 39 (19°9) 161
Smith, C., see Hall 39 (1989) 57
Smulders, H.E., see Denisse 39 (1989) 25
Snell, A.J., J.J. Delima, K.V. Krishna and A.E. Owen, The application of vanadium-doped SiO_2 to EEPROM devices 39 (1989) 368
Spitzer, A. and R. Baunach, The physics of ONO layer dielectrics 39 (1989) 192
Spitzer, A., see Baunach 39 (1989) 200
Stasiak, J., see Batey 39 (1989) 1
Stathis, J.H., see Jousse 39 (1989) 412
Stesmans, A. and G. Van Gorp, Electron spin resonance observation of the interfacial $^{*}Si{\equiv}Si_3$ (P_{b0}) defect in thermally grown (111)Si/Si_3N_4 39 (1989) 317

Takeda, E., A cross section of hot-carrier phenomena in MOS ULSI's 39 (1989) 535
Tatlock, G.T., see Hall 39 (1989) 57
Taylor, S., see Hall 39 (1989) 57
Taylor, S., see Zhang 39 (1989) 374
Tierney, E., see Batey 39 (1989) 1
Trimaille, I. and S. Rigo, Use of ^{18}O isotopic labelling to study thermal dry oxidation of silicon as a function of temperature and pressure 39 (1989) 65
Trimble, L.E., see Celler 39 (1989) 245
Tsu, D.V., see Lucovsky 39 (1989) 33
Tuppen, C., see Hall 39 (1989) 57
Turchanikov, V.I., see Lysenko 39 (1989) 388

Uren, M.J. and M.J. Kirton, The gate-voltage dependence of telegraph noise amplitudes in small MOSFET's 39 (1989) 479

Van der Put, P.J., see Bath 39 (1989) 135
Van der Weg, W.F., see Denisse 39 (1989) 25
Van der Weg, W.F., see Oude Elferink 39 (1989) 219
Van Gorp, G., see Stesmans 39 (1989) 317
Vertoprakhov, V.N., see Salman 39 (1989) 141

Warren, W.L., P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406
Watkinson, P., see Zhang 39 (1989) 374
Weber, W., see Brox 39 (1989) 429
Wei Shan, see Johnson 39 (1989) 301
Wolters, D.R. and A.T.A. Zegers-van Duynhoven, Kinetics of dry oxidation of silicon 39 (1989) 81
Wolters, D.R. and A.T.A. Zegers-van Duynhoven, Trapping of hot electrons 39 (1989) 565
Wong, H. and Y.C. Cheng, Temperature dependence of low-frequency noise in n-channel MOS transistors 39 (1989) 493

Ye, Q.-Y. and F. Koch, Modification of the Si–SiO_2 interface by the degradation–annealing cycle 39 (1989) 339
Yin, X., see Fitch 39 (1989) 103
Young, N.D. and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364
Yu, P.Y., see Johnson 39 (1989) 301

Zakharchuk, N.F., see Belyi 39 (1989) 161
Zegers-van Duynhoven, A.T.A., see Wolters 39 (1989) 81
Zegers-van Duynhoven, A.T.A., see Wolters 39 (1989) 565
Zhang, J.F., see Hall 39 (1989) 57
Zhang, J.F., P. Watkinson, S. Taylor and W. Eccleston, Interface state behaviour of plasma grown oxides following low temperature annealing 39 (1989) 374

Applied Surface Science 39 (1989) 603–614
North-Holland, Amsterdam

SUBJECT INDEX

Alkali metals

W. Bauch, K. Jäger and R. Hezel, Effect of Cs contamination on the interface state density of MNOS capacitors 39 (1989) 356
N.D. Young and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364

Amorphous materials

W.B. Jackson, Defect kinetics in hydrogenated amorphous silicon MIS structures 39 (1989) 273
A.J. Snell, J.J. Delima, K.V. Krishna and A.E. Owen, The application of vanadium-doped SiO_2 to EEPROM devices 39 (1989) 368
P.M. Lenahan, D.T. Krick and J. Kanicki, The nature of the dominant deep trap in amorphous silicon nitride films: evidence for a negative correlation energy 39 (1989) 392

Annealing

S. Prasad and R. Ferretti, Influence of annealing on interfaces of MOS structures with RTO oxides 39 (1989) 348

Auger electron spectroscopy

B. Balland, J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210

Band structure

M.V. Fischetti, S.E. Laux and D.J. DiMaria, The physics of hot-electron degradation of Si MOSFET's: can we understand it? 39 (1989) 578

Boron nitride

A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135

Chemical vapour deposition

J. Batey, E. Tierney, J. Stasiak and T.N. Nguyen, Plasma-enhanced CVD of high quality insulating films 39 (1989) 1
J. Michailos and Y. Cros, Influence of helium dilution on physico-chemical and defect properties of PECVD silicon oxynitride films 39 (1989) 16
C.M.M. Denisse, H.E. Smulders, F.H.P.M. Habraken and W.F. van der Weg, Oxidation of plasma enhanced chemical vapour deposited silicon nitride and oxynitride films 39 (1989) 25
G. Lucovsky, D.V. Tsu, S.S. Kim, R.J. Markunas and G.G. Fountain, Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD) 39 (1989) 33
A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135
Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168
N.D. Young and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364
W.L. Warren, P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406
D. Jousse, J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412

Coatings

J. Gual, J. Samitier, J.R. Morante, J. Anton, P. Boher and M. Renaud, Isolation quality in passivated semi-insulating GaAs analyzed by leakage current transients 39 (1989) 144
J.Y. Longère, K. Schohe, S.K. Krawczyk, R. Schütz and H.L. Hartnagel, Passivation of InP surfaces controlled by photoluminescence measurements 39 (1989) 151
Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168

Cobalt

J. Baten, M. Offenberg, U. Emmerichs, P. Balk, P.J. Grunthaner and S. Ewert, Diffusion of cobalt and titanium in SiO_2 39 (1989) 266

Compound formation

I. Trimaille and S. Rigo, Use of ^{18}O isotopic labelling to study thermal dry oxidation of silicon as a function of temperature and pressure 39 (1989) 65
D.R. Wolters and A.T.A. Zegers-van Duynhoven, Kinetics of dry oxidation of silicon 39 (1989) 81
J.M. deLarios, C.R. Helms, D.B. Kao and B.E. Deal, Parallel oxidation model for Si including both molecular and atomic oxygen mechanisms 39 (1989) 89

Conductivity

M.J. Uren and M.J. Kirton, The gate-voltage dependence of telegraph noise amplitudes in small MOSFET's 39 (1989) 479
O. Jäntsch, Statistics of random telegraph signals in MOSFET's 39 (1989) 486

Diffusion

I. Trimaille and S. Rigo, Use of ^{18}O isotopic labelling to study thermal dry oxidation of silicon as a function of temperature and pressure 39 (1989) 65
G.K. Celler and L.E. Trimble, Formation of SiO at Si/SiO_2 interface and its influence on transport of Group V dopants and Ge in SiO_2 39 (1989) 245
J. Baten, M. Offenberg, U. Emmerichs, P. Balk, P.J. Grunthaner and S. Ewert, Diffusion of cobalt and titanium in SiO_2 39 (1989) 266

Electrical measurements

A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135
E.G. Salman, A.N. Korshunov and V.N. Vertoprakhov, A DLTS study of InAs MIS structures (Extended Abstract) 39 (1989) 141
J. Gual, J. Samitier, J.R. Morante, J. Anton, P. Boher and M. Renaud, Isolation quality in passivated semi-insulating GaAs analyzed by leakage current transients 39 (1989) 144
Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168
W. Hönlein and H. Reisinger, ONO technology 39 (1989) 178
A. Spitzer and R. Baunach, The physics of ONO layer dielectrics 39 (1989) 192
B. Balland, J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210
E.E. Dooms, M.M. Heyns and R.F. De Keersmaecker, Characterization of 30 nm nitrided oxides fabricated by rapid thermal nitridation 39 (1989) 227
V.G. Litovchenko, V.G. Popov and A.A. Evtukh, Characteristics of the insulator–semiconductor (IS) systems with a graded-bandgap insulator at high electric fields 39 (1989) 238
M. Saettler, V. Lauer, M. Offenberg, K. Heyers and P. Balk, Effects of ion implantation on the interfacial properties of MOS systems 39 (1989) 259
M.O. Andersson and O. Engström, Atomic relaxation of $Si–SiO_2$ interface states measured by a photo-depopulation technique 39 (1989) 289
N.M. Johnson, Wei Shan and P.Y. Yu, A test of the dangling-orbital versus overcoordination models for the P_b center at the $Si–SiO_2$ interface 39 (1989) 301
M.M. Heyns, D. Krishna Rao and R.F. De Keersmaecker, Oxide field dependence of $Si–SiO_2$ interface state generation and charge trapping during electron injection 39 (1989) 327
Q.-Y. Ye and F. Koch, Modification of the $Si–SiO_2$ interface by the degradation–annealing cycle 39 (1989) 339
S. Prasad and R. Ferretti, Influence of annealing on interfaces of MOS structures with RTO oxides 39 (1989) 348

W. Bauch, K. Jäger and R. Hezel, Effect of Cs contamination on the interface state density of MNOS capacitors 39 (1989) 356
N.D. Young and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364
A.J. Snell, J.J. Delima, K.V. Krishna and A.E. Owen, The application of vanadium-doped SiO_2 to EEPROM devices 39 (1989) 368
J.F. Zhang, P. Watkinson, S. Taylor and W. Eccleston, Interface state behaviour of plasma grown oxides following low temperature annealing 39 (1989) 374
S.V. Bogdanov, P.P. Povarov, V.E. Shubin and D.A. Shushakov, Investigation of MIS structures using avalanche multiplication 39 (1989) 381
V.S. Lysenko, A.N. Nazarov, I.N. Osiyuk and V.I. Turchanikov, Transformation of Si–SiO_2–Al structures under RF-plasma treatment (Extended Abstract) 39 (1989) 388
P.M. Lenahan, D.T. Krick and J. Kanicki, The nature of the dominant deep trap in amorphous silicon nitride films: evidence for a negative correlation energy 39 (1989) 392
W.L. Warren, P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406
D. Jousse, J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412
D.A. Buchanan, M.V. Fischetti and D.J. DiMaria, Coulombic and neutral electron trapping centers in SiO_2 39 (1989) 420
M. Brox, F. Hofmann and W. Weber, Spatial distribution of damage caused by 6.4 eV photon irradiation in the gate oxide of MOSFET's 39 (1989) 429
H. Wong and Y.C. Cheng, Temperature dependence of low-frequency noise in n-channel MOS transistors 39 (1989) 493
A. Karmann and M. Schulz, Characterization of individual defects in MOSFET's 39 (1989) 500
Y. Nissan-Cohen, The effect of hydrogen on hot carrier and radiation immunity of MOS devices 39 (1989) 511
H.E. Maes, G. Groeseneken, P. Heremans and R. Bellens, Understanding of the hot carrier degradation behaviour of MOSFET's by means of the charge pumping technique 39 (1989) 523
E. Takeda, A cross section of hot-carrier phenomena in MOS ULSI's 39 (1989) 535
S.A. Lyon, Interface states generated by the injection of electrons and holes into SiO_2 39 (1989) 552
D.R. Wolters and A.T.A. Zegers-van Duynhoven, Trapping of hot electrons 39 (1989) 565
M.V. Fischetti, S.E. Laux and D.J. DiMaria, The physics of hot-electron degradation of Si MOSFET's: can we understand it? 39 (1989) 578

Electron diffraction

G.J. Pietsch, M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457

Electron microscopy

W. Hönlein and H. Reisinger, ONO technology 39 (1989) 178

Electron spin resonance

A. Stesmans and G. Van Gorp, Electron spin resonance observation of the interfacial $*Si{\equiv}Si_3$ (P_{b0}) defect in thermally grown (111)Si/Si_3N_4 39 (1989) 317

P.M. Lenahan, D.T. Krick and J. Kanicki, The nature of the dominant deep trap in amorphous silicon nitride films: evidence for a negative correlation energy 39 (1989) 392

W.L. Warren, P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406

D. Jousse, J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412

Ellipsometry

Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168

I.A. Aizenberg, I.R. Moskvina and S.N. Nosenko, The changes in Si surface roughness and their diagnostics 39 (1989) 473

Gallium arsenide

J. Gual, J. Samitier, J.R. Morante, J. Anton, P. Boher and M. Renaud, Isolation quality in passivated semi-insulating GaAs analyzed by leakage current transients 39 (1989) 144

V.I. Belyi, T.P. Smirnova and N.F. Zakharchuk, Phase composition and structure of native oxides on $A^{III}B^{V}$ semiconductors 39 (1989) 161

Hydrogen

W.B. Jackson, Defect kinetics in hydrogenated amorphous silicon MIS structures 39 (1989) 273

Y. Nissan-Cohen, The effect of hydrogen on hot carrier and radiation immunity of MOS devices 39 (1989) 511

Indium antimonide

V.I. Belyi, T.P. Smirnova and N.F. Zakharchuk, Phase composition and structure of native oxides on $A^{III}B^{V}$ semiconductors 39 (1989) 161

Indium arsenide

E.G. Salman, A.N. Korshunov and V.N. Vertoprakhov, A DLTS study of InAs MIS structures (Extended Abstract) 39 (1989) 141

V.I. Belyi, T.P. Smirnova and N.F. Zakharchuk, Phase composition and structure of native oxides on $A^{III}B^{V}$ semiconductors 39 (1989) 161

Indium phosphide

A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135
J.Y. Longère, K. Schohe, S.K. Krawczyk, R. Schütz and H.L. Hartnagel, Passivation of InP surfaces controlled by photoluminescence measurements 39 (1989) 151

Infrared spectroscopy

J.T. Fitch, C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
F. Müller, N. Schwarz, V. Petrova-Koch and F. Koch, Vibration spectroscopy for surface layers on Si 39 (1989) 127
Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168
B. Balland, J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210

Interfaces

J.T. Fitch, C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
K. Brunner, G. Abstreiter, B.O. Kolbesen and H.W. Meul, Strain at $Si-SiO_2$ interfaces studied by micro-Raman spectroscopy 39 (1989) 116
J.Y. Longère, K. Schohe, S.K. Krawczyk, R. Schütz and H.L. Hartnagel, Passivation of InP surfaces controlled by photoluminescence measurements 39 (1989) 151
G.K. Celler and L.E. Trimble, Formation of SiO at Si/SiO_2 interface and its influence on transport of Group V dopants and Ge in SiO_2 39 (1989) 245
N.M. Johnson, Wei Shan and P.Y. Yu, A test of the dangling-orbital versus overcoordination models for the P_b center at the $Si-SiO_2$ interface 39 (1989) 301
A.H. Edwards, A critical assessment of the overcoordination model for the P_b center at the $\langle 111 \rangle$ Si/SiO_2 interface 39 (1989) 309
A. Stesmans and G. Van Gorp, Electron spin resonance observation of the interfacial $^{\bullet}Si{\equiv}Si_3$ (P_{b0}) defect in thermally grown $(111)Si/Si_3N_4$ 39 (1989) 317
Q.-Y. Ye and F. Koch, Modification of the $Si-SiO_2$ interface by the degradation–annealing cycle 39 (1989) 339
G.J. Pietsch, M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457

Ion implantation

M. Saettler, V. Lauer, M. Offenberg, K. Heyers and P. Balk, Effects of ion implantation on the interfacial properties of MOS systems 39 (1989) 259
D.A. Buchanan, M.V. Fischetti and D.J. DiMaria, Coulombic and neutral electron trapping centers in SiO_2 39 (1989) 420

Ion scattering

J.B. Oude Elferink, F.H.P.M. Habraken, W.F. van der Weg, E. Dooms, M. Heyns and R. De Keersmaecker, Rapid thermal nitridation of SiO_2 films 39 (1989) 219
G.K. Celler and L.E. Trimble, Formation of SiO at Si/SiO_2 interface and its influence on transport of Group V dopants and Ge in SiO_2 39 (1989) 245

Light scattering

J.T. Fitch, C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
G.J. Pietsch, M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457

Luminescence

J.Y. Longère, K. Schohe, S.K. Krawczyk, R. Schütz and H.L. Hartnagel, Passivation of InP surfaces controlled by photoluminescence measurements 39 (1989) 151

MOS (metal–oxide–semiconductor) structure

V.G. Litovchenko, V.G. Popov and A.A. Evtukh, Characteristics of the insulator–semiconductor (IS) systems with a graded-bandgap insulator at high electric fields 39 (1989) 238
M. Saettler, V. Lauer, M. Offenberg, K. Heyers and P. Balk, Effects of ion implantation on the interfacial properties of MOS systems 39 (1989) 259
W.B. Jackson, Defect kinetics in hydrogenated amorphous silicon MIS structures 39 (1989) 273
M.O. Andersson and O. Engström, Atomic relaxation of $Si–SiO_2$ interface states measured by a photo-depopulation technique 39 (1989) 289
N.M. Johnson, Wei Shan and P.Y. Yu, A test of the dangling-orbital versus overcoordination models for the P_b center at the $Si–SiO_2$ interface 39 (1989) 301
M.M. Heyns, D. Krishna Rao and R.F. De Keersmaecker, Oxide field dependence of $Si–SiO_2$ interface state generation and charge trapping during electron injection 39 (1989) 327
S. Prasad and R. Ferretti, Influence of annealing on interfaces of MOS structures with RTO oxides 39 (1989) 348
W. Bauch, K. Jäger and R. Hezel, Effect of Cs contamination on the interface state density of MNOS capacitors 39 (1989) 356
S.V. Bogdanov, P.P. Povarov, V.E. Shubin and D.A. Shushakov, Investigation of MIS structures using avalanche multiplication 39 (1989) 381
V.S. Lysenko, A.N. Nazarov, I.N. Osiyuk and V.I. Turchanikov, Transformation of $Si–SiO_2–Al$ structures under RF-plasma treatment (Extended Abstract) 39 (1989) 388
D.A. Buchanan, M.V. Fischetti and D.J. DiMaria, Coulombic and neutral electron trapping centers in SiO_2 39 (1989) 420
M. Brox, F. Hofmann and W. Weber, Spatial distribution of damage caused by 6.4 eV photon irradiation in the gate oxide of MOSFET's 39 (1989) 429

M.J. Uren and M.J. Kirton, The gate-voltage dependence of telegraph noise amplitudes in small MOSFET's 39 (1989) 479
O. Jäntsch, Statistics of random telegraph signals in MOSFET's 39 (1989) 486
H. Wong and Y.C. Cheng, Temperature dependence of low-frequency noise in n-channel MOS transistors 39 (1989) 493
A. Karmann and M. Schulz, Characterization of individual defects in MOSFET's 39 (1989) 500
Y. Nissan-Cohen, The effect of hydrogen on hot carrier and radiation immunity of MOS devices 39 (1989) 511
H.E. Maes, G. Groeseneken, P. Heremans and R. Bellens, Understanding of the hot carrier degradation behaviour of MOSFET's by means of the charge pumping technique 39 (1989) 523
E. Takeda, A cross section of hot-carrier phenomena in MOS ULSI's 39 (1989) 535
S.A. Lyon, Interface states generated by the injection of electrons and holes into SiO_2 39 (1989) 552
D.R. Wolters and A.T.A. Zegers-van Duynhoven, Trapping of hot electrons 39 (1989) 565
M.V. Fischetti, S.E. Laux and D.J. DiMaria, The physics of hot-electron degradation of Si MOSFET's: can we understand it? 39 (1989) 578

Oxides

V.I. Belyi, T.P. Smirnova and N.F. Zakharchuk, Phase composition and structure of native oxides on $A^{III}B^{V}$ semiconductors 39 (1989) 161

Photoconductivity

M.O. Andersson and O. Engström, Atomic relaxation of $Si-SiO_2$ interface states measured by a photo-depopulation technique 39 (1989) 289

Photoelectron spectroscopy

A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135

Plasma processing

J. Batey, E. Tierney, J. Stasiak and T.N. Nguyen, Plasma-enhanced CVD of high quality insulating films 39 (1989) 1
J. Michailos and Y. Cros, Influence of helium dilution on physico-chemical and defect properties of PECVD silicon oxynitride films 39 (1989) 16
C.M.M. Denisse, H.E. Smulders, F.H.P.M. Habraken and W.F. van der Weg, Oxidation of plasma enhanced chemical vapour deposited silicon nitride and oxynitride films 39 (1989) 25
G. Lucovsky, D.V. Tsu, S.S. Kim, R.J. Markunas and G.G. Fountain, Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD) 39 (1989) 33
S. Hall, J.F. Zhang, S. Taylor, W. Eccleston, P. Beahan, G.T. Tatlock, C.J. Gibbings, C. Smith and C. Tuppen, Assessment of plasma-grown oxides on Si : Ge substrates 39 (1989) 57

A. Bath, P.J. van der Put, J. Schoonman and B. Lepley, Study of boron nitride gate insulators grown by low temperature plasma enhanced chemical vapor deposition on InP 39 (1989) 135
N.D. Young and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364
J.F. Zhang, P. Watkinson, S. Taylor and W. Eccleston, Interface state behaviour of plasma grown oxides following low temperature annealing 39 (1989) 374
V.S. Lysenko, A.N. Nazarov, I.N. Osiyuk and V.I. Turchanikov, Transformation of Si–SiO_2–Al structures under RF-plasma treatment (Extended Abstract) 39 (1989) 388
W.L. Warren, P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406
D. Jousse, J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412

Raman scattering

J.T. Fitch, C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
K. Brunner, G. Abstreiter, B.O. Kolbesen and H.W. Meul, Strain at Si–SiO_2 interfaces studied by micro-Raman spectroscopy 39 (1989) 116

Secondary ion mass spectroscopy

Y. Nissan-Cohen, The effect of hydrogen on hot carrier and radiation immunity of MOS devices 39 (1989) 511

Silicon

P.O. Hahn, M. Grundner, A. Schnegg and H. Jacob, Correlation of surface morphology and chemical state of Si surfaces to electrical properties 39 (1989) 436

Silicon nitride

J. Michailos and Y. Cros, Influence of helium dilution on physico-chemical and defect properties of PECVD silicon oxynitride films 39 (1989) 16
C.M.M. Denisse, H.E. Smulders, F.H.P.M. Habraken and W.F. van der Weg, Oxidation of plasma enhanced chemical vapour deposited silicon nitride and oxynitride films 39 (1989) 25
G. Lucovsky, D.V. Tsu, S.S. Kim, R.J. Markunas and G.G. Fountain, Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD) 39 (1989) 33
J. Gual, J. Samitier, J.R. Morante, J. Anton, P. Boher and M. Renaud, Isolation quality in passivated semi-insulating GaAs analyzed by leakage current transients 39 (1989) 144
Y. Le Bellego, J.C. Renaud, P. Blanconnier and J.P. Praseuth, Passivation of GaInAs pin photodiodes by UVCVD SiN_x 39 (1989) 168

W. Hönlein and H. Reisinger, ONO technology 39 (1989) 178
A. Spitzer and R. Baunach, The physics of ONO layer dielectrics 39 (1989) 192
R. Baunach and A. Spitzer, Simulation of charge transport and trapping in MIS structures with triple-layer dielectrics 39 (1989) 200
B. Balland, J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210
J.B. Oude Elferink, F.H.P.M. Habraken, W.F. van der Weg, E. Dooms, M. Heyns and R. De Keersmaecker, Rapid thermal nitridation of SiO_2 films 39 (1989) 219
E.E. Dooms, M.M. Heyns and R.F. De Keersmaecker, Characterization of 30 nm nitrided oxides fabricated by rapid thermal nitridation 39 (1989) 227
V.G. Litovchenko, V.G. Popov and A.A. Evtukh, Characteristics of the insulator–semiconductor (IS) systems with a graded-bandgap insulator at high electric fields 39 (1989) 238
A. Stesmans and G. Van Gorp, Electron spin resonance observation of the interfacial $^{\bullet}Si{\equiv}Si_3$ (P_{b0}) defect in thermally grown (111)Si/Si_3N_4 39 (1989) 317
P.M. Lenahan, D.T. Krick and J. Kanicki, The nature of the dominant deep trap in amorphous silicon nitride films: evidence for a negative correlation energy 39 (1989) 392
D. Jousse, J. Kanicki and J.H. Stathis, Electron spin resonance study of metal–nitride–silicon structures: observation of Si dangling bonds with different configurations and trapping properties in silicon nitride 39 (1989) 412

Silicon oxide

J. Batey, E. Tierney, J. Stasiak and T.N. Nguyen, Plasma-enhanced CVD of high quality insulating films 39 (1989) 1
J. Michailos and Y. Cros, Influence of helium dilution on physico-chemical and defect properties of PECVD silicon oxynitride films 39 (1989) 16
C.M.M. Denisse, H.E. Smulders, F.H.P.M. Habraken and W.F. van der Weg, Oxidation of plasma enhanced chemical vapour deposited silicon nitride and oxynitride films 39 (1989) 25
G. Lucovsky, D.V. Tsu, S.S. Kim, R.J. Markunas and G.G. Fountain, Formation of thin film dielectrics by remote plasma-enhanced chemical-vapor deposition (remote PECVD) 39 (1989) 33
S. Hall, J.F. Zhang, S. Taylor, W. Eccleston, P. Beahan, G.T. Tatlock, C.J. Gibbings, C. Smith and C. Tuppen, Assessment of plasma-grown oxides on Si : Ge substrates 39 (1989) 57
I. Trimaille and S. Rigo, Use of ^{18}O isotopic labelling to study thermal dry oxidation of silicon as a function of temperature and pressure 39 (1989) 65
D.R. Wolters and A.T.A. Zegers-van Duynhoven, Kinetics of dry oxidation of silicon 39 (1989) 81
J.M. deLarios, C.R. Helms, D.B. Kao and B.E. Deal, Parallel oxidation model for Si including both molecular and atomic oxygen mechanisms 39 (1989) 89
J.T. Fitch, C.H. Bjorkman, G. Lucovsky, F.H. Pollak and X. Yin, Local atomic structure at thermally grown Si/SiO_2 interfaces 39 (1989) 103
K. Brunner, G. Abstreiter, B.O. Kolbesen and H.W. Meul, Strain at $Si–SiO_2$ interfaces studied by micro-Raman spectroscopy 39 (1989) 116
F. Müller, N. Schwarz, V. Petrova-Koch and F. Koch, Vibration spectroscopy for surface layers on Si 39 (1989) 127

W. Hönlein and H. Reisinger, ONO technology 39 (1989) 178
A. Spitzer and R. Baunach, The physics of ONO layer dielectrics 39 (1989) 192
R. Baunach and A. Spitzer, Simulation of charge transport and trapping in MIS structures with triple-layer dielectrics 39 (1989) 200
B. Balland, J.C. Bureau, A. Benamar, J.J. Dubray and A. Glachant, Effects of addition of oxygen and water vapor in high thermal nitridation processes of SiO_2 thin films 39 (1989) 210
J.B. Oude Elferink, F.H.P.M. Habraken, W.F. van der Weg, E. Dooms, M. Heyns and R. De Keersmaecker, Rapid thermal nitridation of SiO_2 films 39 (1989) 219
E.E. Dooms, M.M. Heyns and R.F. De Keersmaecker, Characterization of 30 nm nitrided oxides fabricated by rapid thermal nitridation 39 (1989) 227
V.G. Litovchenko, V.G. Popov and A.A. Evtukh, Characteristics of the insulator–semiconductor (IS) systems with a graded-bandgap insulator at high electric fields 39 (1989) 238
G.K. Celler and L.E. Trimble, Formation of SiO at Si/SiO_2 interface and its influence on transport of Group V dopants and Ge in SiO_2 39 (1989) 245
J. Baten, M. Offenberg, U. Emmerichs, P. Balk, P.J. Grunthaner and S. Ewert, Diffusion of cobalt and titanium in SiO_2 39 (1989) 266
A.H. Edwards, A critical assessment of the overcoordination model for the P_b center at the $\langle 111 \rangle$ Si/SiO_2 interface 39 (1989) 309
Q.-Y. Ye and F. Koch, Modification of the $Si–SiO_2$ interface by the degradation–annealing cycle 39 (1989) 339
N.D. Young and A. Gill, Mobile ion instabilities in polycrystalline silicon thin film transistors 39 (1989) 364
A.J. Snell, J.J. Delima, K.V. Krishna and A.E. Owen, The application of vanadium-doped SiO_2 to EEPROM devices 39 (1989) 368
J.F. Zhang, P. Watkinson, S. Taylor and W. Eccleston, Interface state behaviour of plasma grown oxides following low temperature annealing 39 (1989) 374
W.L. Warren, P.M. Lenahan and B. Robinson, Fundamental differences in the nature of electrically active point-defects in plasma enhanced chemical vapor deposited and thermal oxide structures 39 (1989) 406
G.J. Pietsch, M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457
I.A. Aizenberg, I.R. Moskvina and S.N. Nosenko, The changes in Si surface roughness and their diagnostics 39 (1989) 473
M.J. Uren and M.J. Kirton, The gate-voltage dependence of telegraph noise amplitudes in small MOSFET's 39 (1989) 479
O. Jäntsch, Statistics of random telegraph signals in MOSFET's 39 (1989) 486

Surface morphology

P.O. Hahn, M. Grundner, A. Schnegg and H. Jacob, Correlation of surface morphology and chemical state of Si surfaces to electrical properties 39 (1989) 436

Surface roughness

P.O. Hahn, M. Grundner, A. Schnegg and H. Jacob, Correlation of surface morphology and chemical state of Si surfaces to electrical properties 39 (1989) 436

G.J. Pietsch, M. Henzler and P.O. Hahn, Continuous roughness characterization from atomic to micron distances: angle-resolved electron and photon scattering 39 (1989) 457
I.A. Aizenberg, I.R. Moskvina and S.N. Nosenko, The changes in Si surface roughness and their diagnostics 39 (1989) 473

Surface and interface states

M.O. Andersson and O. Engström, Atomic relaxation of $Si-SiO_2$ interface states measured by a photo-depopulation technique 39 (1989) 289
N.M. Johnson, Wei Shan and P.Y. Yu, A test of the dangling-orbital versus overcoordination models for the P_b center at the $Si-SiO_2$ interface 39 (1989) 301
A.H. Edwards, A critical assessment of the overcoordination model for the P_b center at the $\langle 111 \rangle$ Si/SiO_2 interface 39 (1989) 309
M.M. Heyns, D. Krishna Rao and R.F. De Keersmaecke, Oxide field dependence of $Si-SiO_2$ interface state generation and charge trapping during electron injection 39 (1989) 327
W. Bauch, K. Jäger and R. Hezel, Effect of Cs contamination on the interface state density of MNOS capacitors 39 (1989) 356
J.F. Zhang, P. Watkinson, S. Taylor and W. Eccleston, Interface state behaviour of plasma grown oxides following low temperature annealing 39 (1989) 374
O. Jäntsch, Statistics of random telegraph signals in MOSFET's 39 (1989) 486
S.A. Lyon, Interface states generated by the injection of electrons and holes into SiO_2 39 (1989) 552

Titanium

J. Baten, M. Offenberg, U. Emmerichs, P. Balk, P.J. Grunthaner and S. Ewert, Diffusion of cobalt and titanium in SiO_2 39 (1989) 266

Vanadium

A.J. Snell, J.J. Delima, K.V. Krishna and A.E. Owen, The application of vanadium-doped SiO_2 to EEPROM devices 39 (1989) 368